

Silicon Diffused Power Transistor

BU2520DF

GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor with an integrated damper diode in a full plastic envelope intended for use in horizontal deflection circuits of large screen colour television receivers.

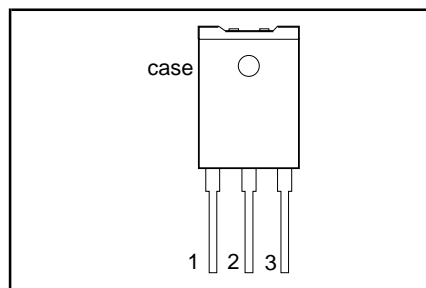
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-------------|---------------------------------------|--|------|------|---------------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0\text{ V}$ | - | 1500 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | - | 800 | V |
| I_C | Collector current (DC) | | - | 10 | A |
| I_{CM} | Collector current peak value | | - | 25 | A |
| P_{tot} | Total power dissipation | $T_{hs} \leq 25\text{ °C}$ | - | 45 | W |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$ | - | 5.0 | V |
| I_{Csat} | Collector saturation current | | 6 | - | A |
| V_F | Diode forward voltage | $I_F = 6.0\text{ A}$ | - | 2.2 | V |
| t_f | Fall time | $I_{Csat} = 6.0\text{ A}; I_{B(end)} = 1.0\text{ A}$ | 0.35 | 0.5 | μs |

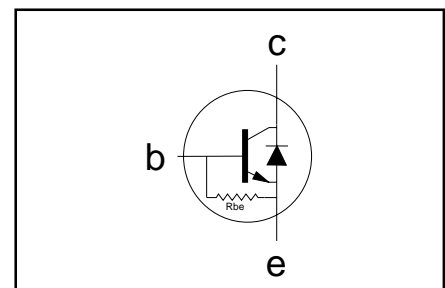
PINNING - SOT199

| PIN | DESCRIPTION |
|------|-------------|
| 1 | base |
| 2 | collector |
| 3 | emitter |
| case | isolated |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------|--|-------------------------------|------|------|--------------------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0\text{ V}$ | - | 1500 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | - | 800 | V |
| I_C | Collector current (DC) | | - | 10 | A |
| I_{CM} | Collector current peak value | | - | 25 | A |
| I_B | Base current (DC) | | - | 6 | A |
| I_{BM} | Base current peak value | | - | 9 | A |
| $-I_{B(AV)}$ | Reverse base current | average over any 20 ms period | - | 150 | mA |
| $-I_{BM}$ | Reverse base current peak value ¹ | | - | 6 | A |
| P_{tot} | Total power dissipation | $T_{hs} \leq 25\text{ °C}$ | - | 45 | W |
| T_{stg} | Storage temperature | | -65 | 150 | $^{\circ}\text{C}$ |
| T_j | Junction temperature | | - | 150 | $^{\circ}\text{C}$ |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|----------------------|------------------------|------|------|------|
| $R_{th\ j-hs}$ | Junction to heatsink | with heatsink compound | - | 2.8 | K/W |
| $R_{th\ j-a}$ | Junction to ambient | in free air | 35 | - | K/W |

¹ Turn-off current.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------|---|---------------------------------------|------|------|------|------|
| V_{isol} | Repetitive peak voltage from all three terminals to external heatsink | R.H. $\leq 65\%$; clean and dustfree | - | | 2500 | V |
| C_{isol} | Capacitance from T2 to external heatsink | $f = 1\text{ MHz}$ | - | 22 | - | pF |

STATIC CHARACTERISTICS

 $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|--|--|------|------|------|----------|
| I_{CES} | Collector cut-off current ² | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ | - | - | 1.0 | mA |
| I_{CES} | | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$ | - | - | 2.0 | mA |
| I_{EBO} | Emitter cut-off current | $V_{EB} = 7.5\text{ V}; I_C = 0\text{ A}$ | 100 | - | 300 | mA |
| BV_{EBO} | Emitter-base breakdown voltage | $I_B = 600\text{ mA}$ | 7.5 | 13.5 | - | V |
| R_{be} | Base-emitter resistance | $V_{EB} = 7.5\text{ V}$ | - | 50 | - | Ω |
| $V_{CEOsust}$ | Collector-emitter sustaining voltage | $I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$ | 800 | - | - | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$ | - | - | 5.0 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$ | - | - | 1.1 | V |
| h_{FE} | DC current gain | $I_C = 1.0\text{ A}; V_{CE} = 5\text{ V}$ | - | 13 | - | |
| h_{FE} | Diode forward voltage | $I_C = 6\text{ A}; V_{CE} = 5\text{ V}$ | 5 | 7 | 9.5 | |
| V_F | | $I_F = 6\text{ A}$ | - | - | 2.2 | V |

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|--------|--|--|------|------|---------------|
| C_c | Collector capacitance | $I_E = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | 115 | - | pF |
| | Switching times (16 kHz line deflection circuit) | $I_{Csat} = 6.0\text{ A}; L_C = 650\text{ }\mu\text{H}; C_{fb} = 19\text{ nF};$ $I_{B(end)} = 1.0\text{ A}; L_B = 5.3\text{ }\mu\text{H}; -V_{BB} = 4\text{ V};$ $(-di_B/dt = 0.8\text{ A}/\mu\text{s})$ | | | |
| t_s | Turn-off storage time | | 4.5 | 5.5 | μs |
| t_f | Turn-off fall time | | 0.35 | 0.5 | μs |

² Measured with half sine-wave voltage (curve tracer).

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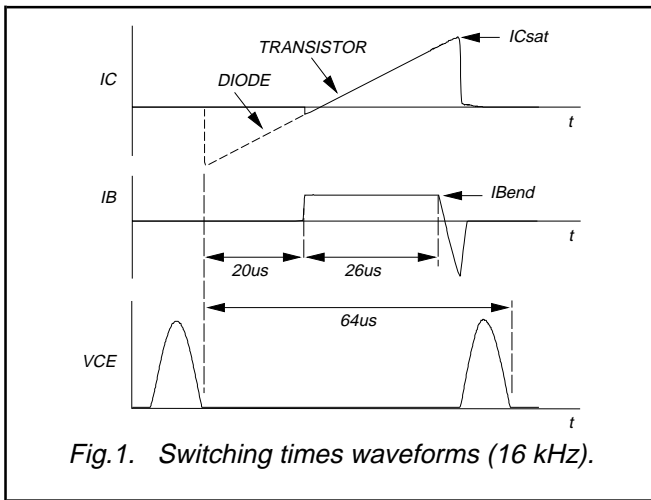


Fig.1. Switching times waveforms (16 kHz).

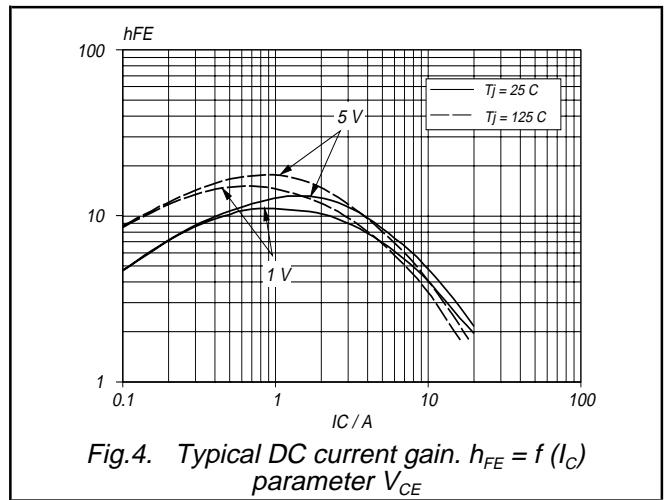


Fig.4. Typical DC current gain. $h_{FE} = f(I_C)$ parameter V_{CE}

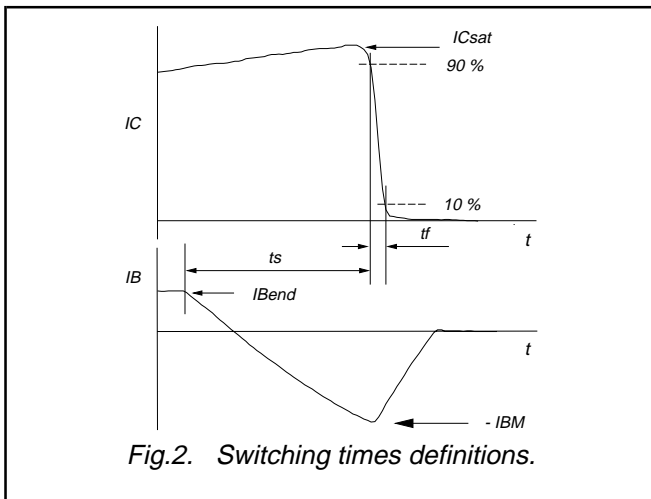


Fig.2. Switching times definitions.

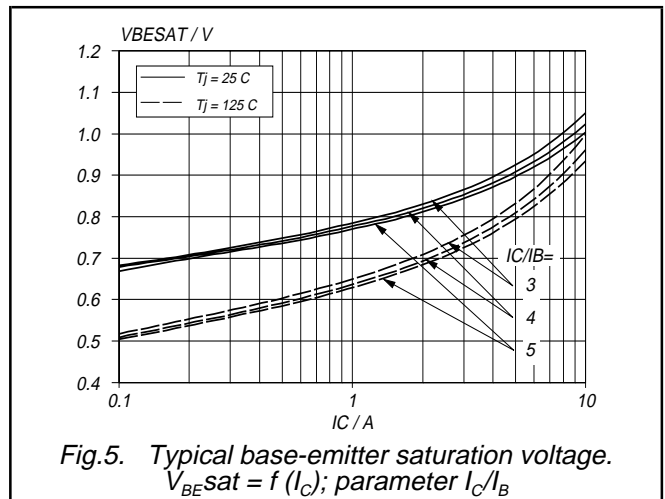


Fig.5. Typical base-emitter saturation voltage. $V_{BEsat} = f(I_C)$; parameter I_C/I_B

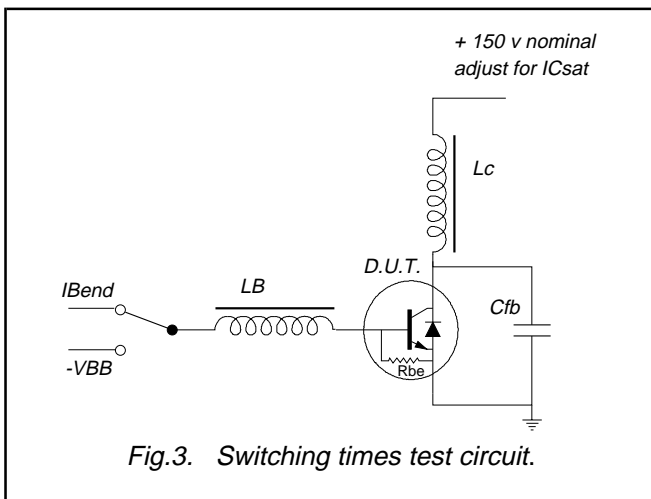


Fig.3. Switching times test circuit.

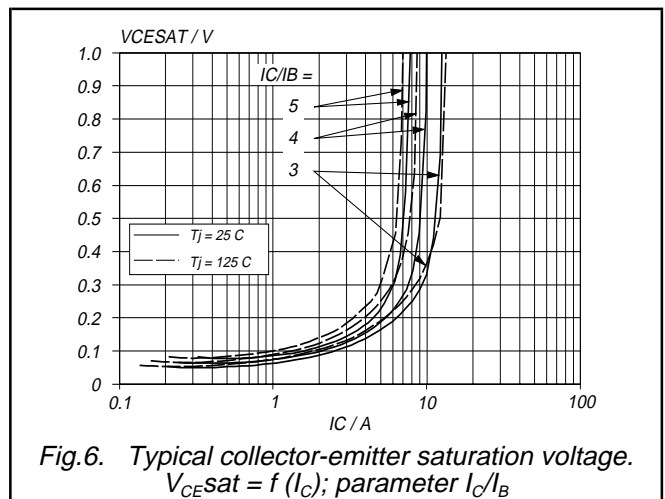
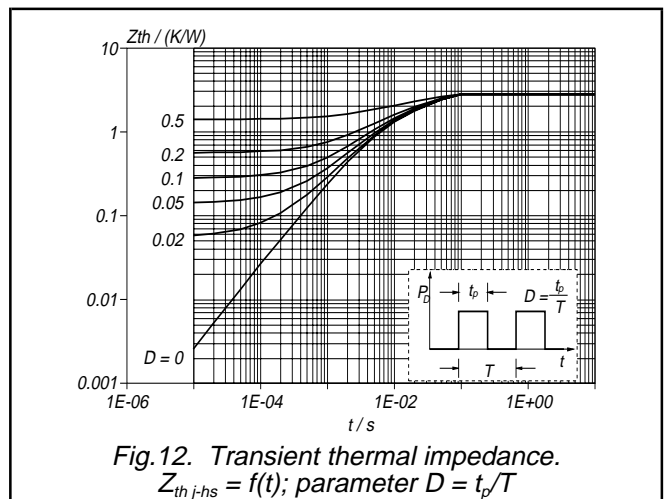
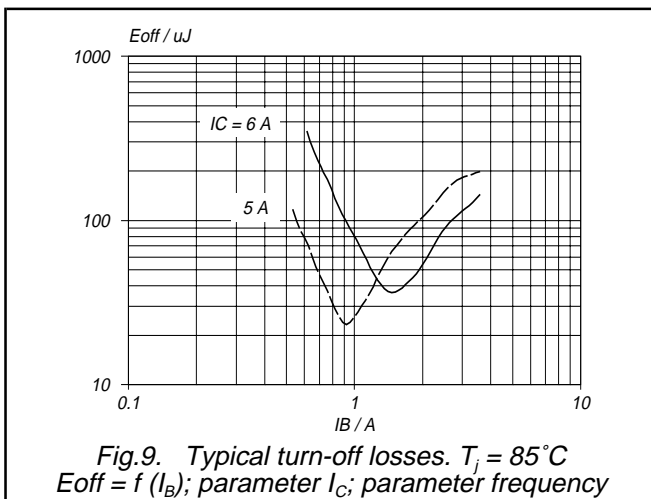
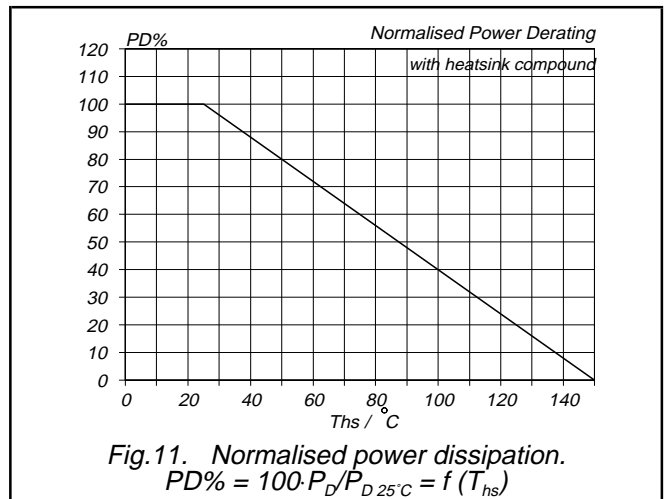
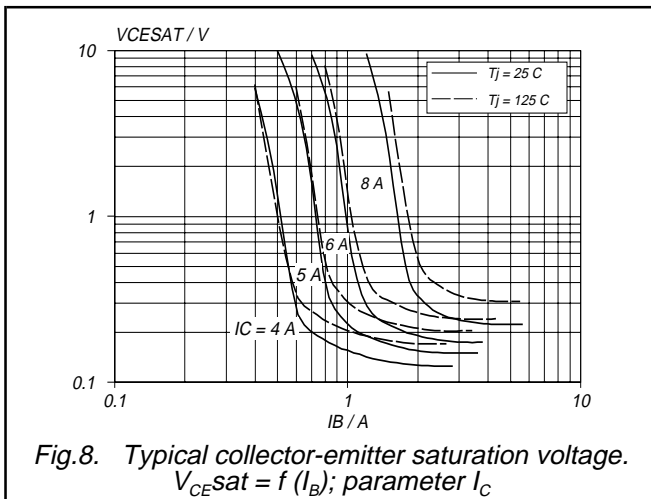
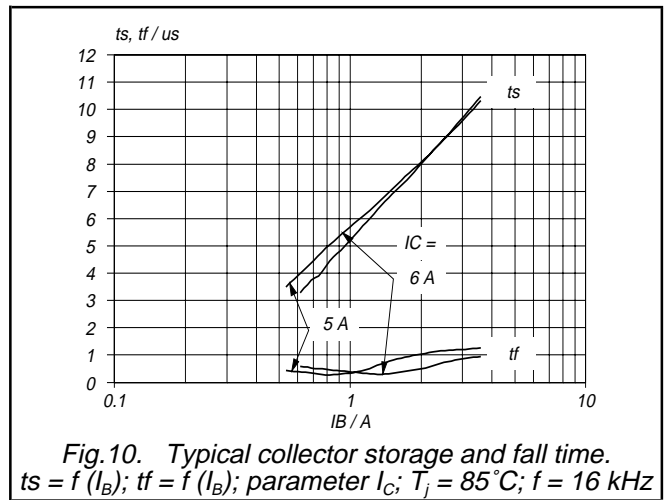
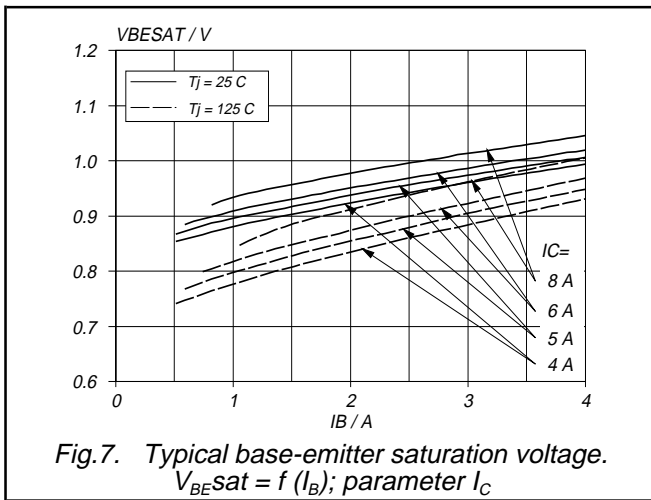


Fig.6. Typical collector-emitter saturation voltage. $V_{CESat} = f(I_C)$; parameter I_C/I_B

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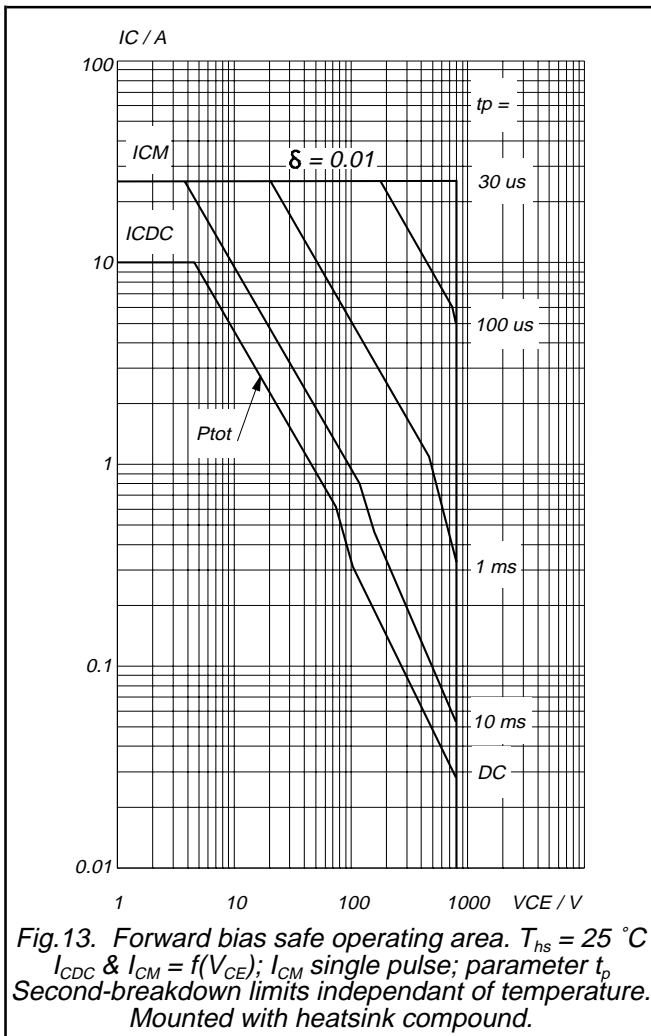
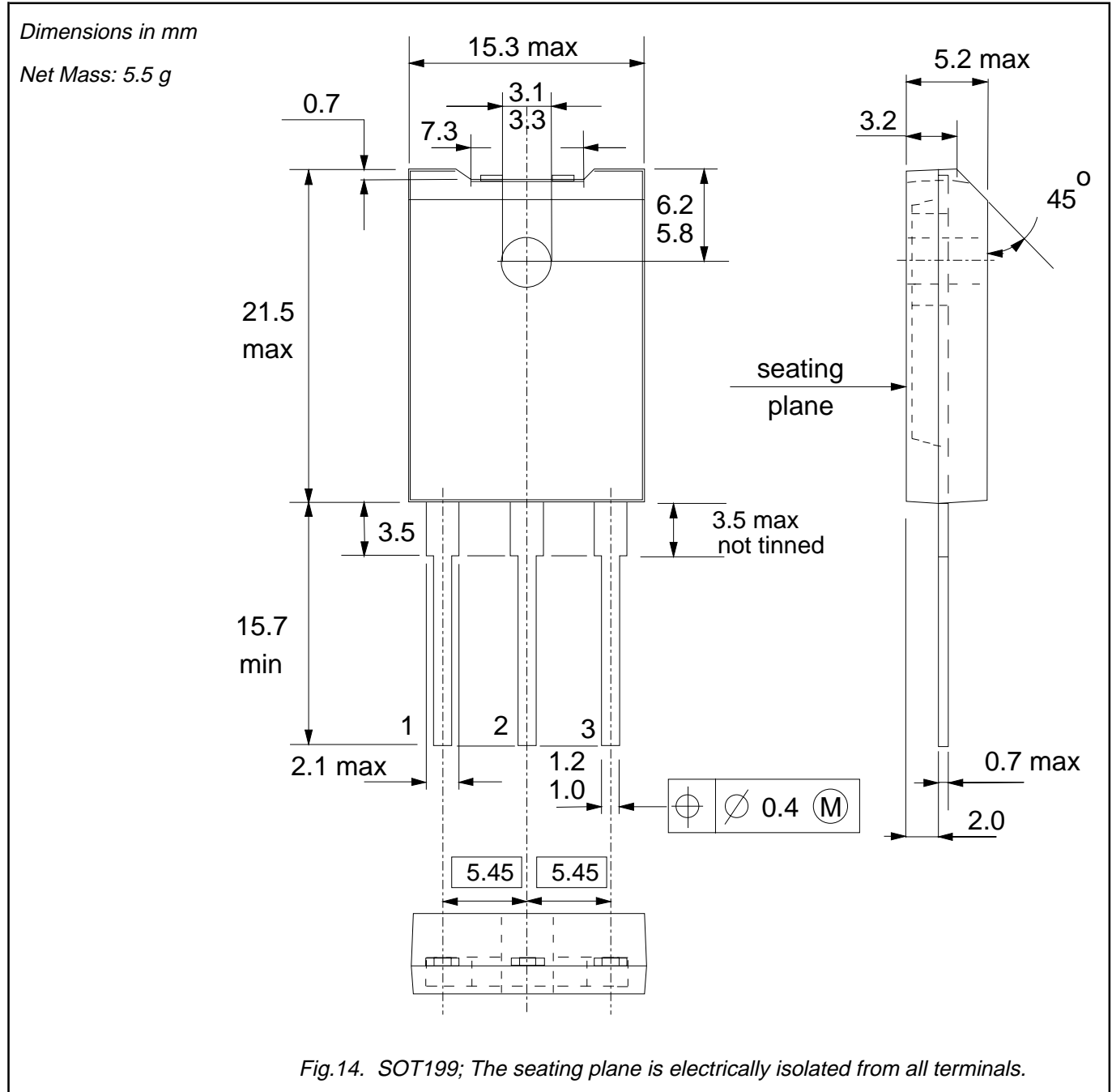


Fig.13. Forward bias safe operating area. $T_{hs} = 25\text{ }^\circ\text{C}$
 I_{CDC} & $I_{CM} = f(V_{CE})$; I_{CM} single pulse; parameter t_p
 Second-breakdown limits independent of temperature.
 Mounted with heatsink compound.

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MECHANICAL DATA



Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
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